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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	4075
Number of Logic Elements/Cells	52160
Total RAM Bits	2764800
Number of I/O	210
Number of Gates	-
Voltage - Supply	0.95V ~ 1.05V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	324-LFBGA, CSPBGA
Supplier Device Package	324-CSPBGA (15x15)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7a50t-l2csg324e

Table 1: **Absolute Maximum Ratings[(1)] *(Cont'd)***

Symbol	Description	Min	Max	Units
Temperature				
T_{STG}	Storage temperature (ambient)	–65	150	°C
T_{SOL}	Maximum soldering temperature for Pb/Sn component bodies [(6)]	–	+220	°C
	Maximum soldering temperature for Pb-free component bodies [(6)]	–	+260	°C
T_j	Maximum junction temperature[(6)]	–	+125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. The lower absolute voltage specification always applies.
3. For I/O operation, refer to UG471: *7 Series FPGAs SelectIO Resources User Guide*.
4. The maximum limit applied to DC signals.
5. For maximum undershoot and overshoot AC specifications, see Table 4.
6. For soldering guidelines and thermal considerations, see UG475: *7 Series FPGA Packaging and Pinout Specification*.

Table 2: **Recommended Operating Conditions[(1)(2)]**

Symbol	Description	Min	Typ	Max	Units
FPGA Logic					
V_{CCINT}	Internal supply voltage	0.95	1.00	1.05	V
	For -2L (0.9V) devices: internal supply voltage	0.87	0.90	0.93	V
V_{CCAUX}	Auxiliary supply voltage	1.71	1.80	1.89	V
V_{CCBRAM}	Block RAM supply voltage	0.95	1.00	1.05	V
V_{CCO}[(3)(4)]	Supply voltage for 3.3V HR I/O banks	1.14	–	3.465	V
V_{IN}[(5)]	I/O input voltage	–0.20	–	V_{CCO} + 0.20	V
	I/O input voltage for V_{REF} and differential I/O standards	–0.20	–	2.625	V
I_{IN}[(6)]	Maximum current through any pin in a powered or unpowered bank when forward biasing the clamp diode.	–	–	10	mA
V_{CCBATT}[(7)]	Battery voltage	1.0	–	1.89	V
GTP Transceiver					
$V_{MGTAVCC}$[(8)(9)]	Analog supply voltage for the GTP transmitter and receiver circuits	0.97	1.0	1.03	V
$V_{MGTAVTT}$[(8)(9)]	Analog supply voltage for the GTP transmitter and receiver termination circuits	1.17	1.2	1.23	V
XADC					
V_{CCADC}	XADC supply relative to GNDADC	1.71	1.80	1.89	V
V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V

Table 2: **Recommended Operating Conditions[1][2] *(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
Temperature					
T_j	Junction temperature operating range for commercial (C) temperature devices	0	–	85	°C
	Junction temperature operating range for extended (E) temperature devices	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices	–40	–	100	°C

Notes:

1. All voltages are relative to ground.
2. For the design of the power distribution system consult UG483, *7 Series FPGAs PCB Design and Pin Planning Guide*.
3. Configuration data is retained even if V_{CCO} drops to 0V.
4. Includes V_{CCO} of 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V.
5. The lower absolute voltage specification always applies.
6. A total of 200 mA per bank should not be exceeded.
7. V_{CCBATT} is required only when using bitstream encryption. If battery is not used, connect V_{CCBATT} to either ground or V_{CCAUX}.
8. Each voltage listed requires the filter circuit described in UG482: *7 Series FPGAs GTP Transceiver User Guide*.
9. Voltages are specified for the temperature range of T_j = 0°C to +85°C.

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ[1]	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested)	–	–	15	µA
C_{IN}[2]	Die input capacitance at the pad	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 3.3V	90	–	330	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 2.5V	68	–	250	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.8V	34	–	220	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.5V	23	–	150	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.2V	12	–	120	µA
I_{RPD}	Pad pull-down (when selected) @ V_{IN} = 3.3V	68	–	330	µA
	Pad pull-down (when selected) @ V_{IN} = 1.8V	45	–	180	µA
I_{CCADC}	Analog supply current, analog circuits in powered up state	–	–	25	mA
I_{BATT}[3]	Battery supply current	–	–	150	nA
R_{IN_TERM}[4]	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_40) for commercial (C), and industrial (I), and extended (E) temperature devices	28	40	55	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_50) for commercial (C), and industrial (I), and extended (E) temperature devices	35	50	65	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_60) for commercial (C), and industrial (I), and extended (E) temperature devices	44	60	83	Ω

Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCBRAM}, V_{CCAUX}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCBRAM} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously. If V_{CCAUX} and V_{CCO} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously.

For V_{CCO} voltages of 3.3V in HR I/O banks and configuration bank 0:

- The voltage difference between V_{CCO} and V_{CCAUX} must not exceed 2.625V for longer than $T_{VCCO2VCCAUX}$ for each power-on/off cycle to maintain device reliability levels.
- The $T_{VCCO2VCCAUX}$ time can be allocated in any percentage between the power-on and power-off ramps.

The recommended power-on sequence to achieve minimum current draw for the GTP transceivers is V_{CCINT}, $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT}, $V_{MGTAVTT}$. There is no recommended sequencing for $V_{MGTVCCAUX}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

- When $V_{MGTAVTT}$ is powered before $V_{MGTAVCC}$ and $V_{MGTAVTT} – V_{MGTAVCC}$ > 150 mV and $V_{MGTAVCC}$ < 0.7V, the $V_{MGTAVTT}$ current draw can increase by 460 mA per transceiver during $V_{MGTAVCC}$ ramp up. The duration of the current draw can be up to 0.3 x $T_{MGTAVCC}$ (ramp time from GND to 90% of $V_{MGTAVCC}$). The reverse is true for power-down.
- When $V_{MGTAVTT}$ is powered before V_{CCINT} and $V_{MGTAVTT} – V_{CCINT}$ > 150 mV and V_{CCINT} < 0.7V, the $V_{MGTAVTT}$ current draw can increase by 50 mA per transceiver during V_{CCINT} ramp up. The duration of the current draw can be up to 0.3 x T_{VCCINT} (ramp time from GND to 90% of V_{CCINT}). The reverse is true for power-down.

Table 6 shows the minimum current, in addition to I_{CCQ}, that is required by Artix-7 devices for proper power-on and configuration. If the current minimums shown in Table 5 and Table 6 are met, the device powers on after all four supplies have passed through their power-on reset threshold voltages. The FPGA must not be configured until after V_{CCINT} is applied.

Once initialized and configured, use the Xilinx Power Estimator (XPE) tools to estimate current drain on these supplies.

Table 6: **Power-On Current for Artix-7 Devices**[1]

Device	$I_{CCINTMIN}$	$I_{CCAUXMIN}$	I_{CCOMIN}	$I_{CCBRAMMIN}$	Units
	Typ[2]	Typ[2]	Typ[2]	Typ[2]	
XC7A100T	I_{CCINTQ} + 170	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XC7A200T	I_{CCINTQ} + 340	I_{CCAUXQ} + 50	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 80	mA

Notes:

1. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at http://www.xilinx.com/power) to calculate maximum power-on currents.
2. Typical values are specified at nominal voltage, 25°C.

Table 7: **Power Supply Ramp Time**

Symbol	Description	Conditions	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 90% of V_{CCINT}		0.2	50	ms
T_{VCCO}	Ramp time from GND to 90% of V_{CCO}		0.2	50	ms
T_{VCCAUX}	Ramp time from GND to 90% of V_{CCAUX}		0.2	50	ms
$T_{VCCBRAM}$	Ramp time from GND to 90% of V_{CCBRAM}		0.2	50	ms
$T_{VCCO2VCCAUX}$	Allowed time per power cycle for $V_{CCO} - V_{CCAUX} > 2.625V$	T_J = 100°C[1]	–	500	ms
		T_J = 85°C[1]	–	800	
$T_{MGTAVCC}$	Ramp time from GND to 90% of $V_{MGTAVCC}$		0.2	50	ms
$T_{MGTAVTT}$	Ramp time from GND to 90% of $V_{MGTAVTT}$		0.2	50	ms

Notes:

1. Based on 240,000 power cycles with nominal V_{CCO} of 3.3V or 36,500 power cycles with worst case V_{CCO} of 3.465V.

Speed Grade Designations

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device. Table 12 correlates the current status of each Artix-7 device on a per speed grade basis.

Table 12: **Artix-7 Device Speed Grade Designations**

Device	Speed Grade Designations		
	Advance	Preliminary	Production
XC7A100T	-2L (0.9V)		-3, -2, -2L (1.0V), -1
XC7A200T	-2L (0.9V)		-3, -2, -2L (1.0V), -1

Production Silicon and ISE Software Status

In some cases, a particular family member (and speed grade) is released to production before a speed specification is released with the correct label (Advance, Preliminary, Production). Any labeling discrepancies are corrected in subsequent speed specification releases.

Table 13 lists the production released Artix-7 device, speed grade, and the minimum corresponding supported speed specification version and ISE software revisions. The ISE software and speed specifications listed are the minimum releases required for production. All subsequent releases of software and speed specifications are valid.

Table 13: **Artix-7 Device Production Software and Speed Specification Release**

Device	Speed Grade			
	1.0V			0.9V
	-3	-2/-2L	-1	-2L
XC7A100T	ISE 14.4 and Vivado 2012.4 with the 14.4/2012.4 device pack v1.07			
XC7A200T	ISE 14.4 and Vivado 2012.4 with the 14.4/2012.4 device pack v1.07			

Notes:
1. Blank entries indicate a device and/or speed grade in advance or preliminary status.

IOB Pad Input/Output/3-State

Table 16 summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- T_{IOPI} is described as the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- T_{IOOP} is described as the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- T_{IOTP} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HR I/O banks, the IN_TERM termination turn-on time is always faster than T_{IOTP} when the INTERMDISABLE pin is used.

Table 16: **3.3V IOB High Range (HR) Switching Characteristics**

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
LVTTL_S4	1.26	1.34	1.41	1.58	3.80	3.93	4.18	4.41	4.37	4.59	5.01	5.06	ns
LVTTL_S8	1.26	1.34	1.41	1.58	3.54	3.66	3.92	4.15	4.11	4.32	4.75	4.80	ns
LVTTL_S12	1.26	1.34	1.41	1.58	3.52	3.65	3.90	4.13	4.09	4.31	4.73	4.78	ns
LVTTL_S16	1.26	1.34	1.41	1.58	3.07	3.19	3.45	3.68	3.64	3.85	4.28	4.33	ns
LVTTL_S24	1.26	1.34	1.41	1.58	3.29	3.41	3.67	3.90	3.86	4.07	4.50	4.55	ns
LVTTL_F4	1.26	1.34	1.41	1.58	3.26	3.38	3.64	3.86	3.83	4.04	4.46	4.51	ns
LVTTL_F8	1.26	1.34	1.41	1.58	2.74	2.87	3.12	3.35	3.31	3.52	3.95	4.00	ns
LVTTL_F12	1.26	1.34	1.41	1.58	2.73	2.85	3.10	3.33	3.29	3.51	3.93	3.98	ns
LVTTL_F16	1.26	1.34	1.41	1.58	2.55	2.68	2.93	3.16	3.12	3.34	3.76	3.81	ns
LVTTL_F24	1.26	1.34	1.41	1.58	2.52	2.65	2.90	3.22	3.09	3.31	3.73	3.87	ns
LVDS_25	0.73	0.81	0.88	0.90	1.29	1.41	1.67	1.86	1.86	2.07	2.49	2.51	ns
MINI_LVDS_25	0.73	0.81	0.88	0.90	1.27	1.40	1.65	1.88	1.84	2.06	2.48	2.53	ns
BLVDS_25	0.73	0.81	0.88	0.90	1.84	1.96	2.21	2.44	2.40	2.62	3.04	3.09	ns
RSDS_25 (point to point)	0.73	0.81	0.88	0.90	1.27	1.40	1.65	1.88	1.84	2.06	2.48	2.53	ns
PPDS_25	0.73	0.81	0.88	0.90	1.29	1.41	1.67	1.88	1.86	2.07	2.49	2.53	ns
TMDS_33	0.73	0.81	0.88	0.90	1.41	1.54	1.79	1.99	1.98	2.20	2.62	2.64	ns
PCI33_3	1.24	1.32	1.39	1.57	3.10	3.22	3.48	3.71	3.67	3.88	4.31	4.36	ns
HSUL_12	0.67	0.75	0.82	0.87	1.80	1.93	2.18	2.41	2.37	2.59	3.01	3.06	ns
DIFF_HSUL_12	0.68	0.76	0.83	0.88	1.80	1.93	2.18	2.21	2.37	2.59	3.01	2.86	ns
HSTL_I_S	0.67	0.75	0.82	0.87	1.62	1.74	1.99	2.19	2.19	2.40	2.82	2.84	ns
HSTL_II_S	0.65	0.73	0.80	0.85	1.41	1.54	1.79	1.99	1.98	2.20	2.62	2.64	ns
HSTL_I_18_S	0.67	0.75	0.82	0.87	1.29	1.41	1.67	1.86	1.86	2.07	2.49	2.51	ns
HSTL_II_18_S	0.66	0.75	0.81	0.87	1.41	1.54	1.79	1.97	1.98	2.20	2.62	2.62	ns
DIFF_HSTL_I_S	0.68	0.76	0.83	0.85	1.59	1.71	1.96	2.13	2.15	2.37	2.79	2.78	ns
DIFF_HSTL_II_S	0.68	0.76	0.83	0.85	1.51	1.63	1.88	2.07	2.08	2.29	2.71	2.72	ns
DIFF_HSTL_I_18_S	0.71	0.79	0.86	0.87	1.38	1.51	1.76	1.96	1.95	2.17	2.59	2.61	ns
DIFF_HSTL_II_18_S	0.70	0.78	0.85	0.87	1.46	1.58	1.84	2.00	2.03	2.24	2.67	2.65	ns
HSTL_I_F	0.67	0.75	0.82	0.87	1.10	1.22	1.48	1.69	1.67	1.88	2.31	2.34	ns

Table 16: **3.3V IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
HSTL_II_F	0.65	0.73	0.80	0.85	1.12	1.24	1.49	1.71	1.69	1.90	2.32	2.36	ns
HSTL_I_18_F	0.67	0.75	0.82	0.87	1.13	1.26	1.51	1.72	1.70	1.92	2.34	2.37	ns
HSTL_II_18_F	0.66	0.75	0.81	0.87	1.12	1.24	1.49	1.71	1.69	1.90	2.32	2.36	ns
DIFF_HSTL_I_F	0.68	0.76	0.83	0.85	1.18	1.30	1.56	1.77	1.75	1.96	2.39	2.42	ns
DIFF_HSTL_II_F	0.68	0.76	0.83	0.85	1.21	1.33	1.59	1.77	1.78	1.99	2.42	2.42	ns
DIFF_HSTL_I_18_F	0.71	0.79	0.86	0.87	1.21	1.33	1.59	1.77	1.78	1.99	2.42	2.42	ns
DIFF_HSTL_II_18_F	0.70	0.78	0.85	0.87	1.21	1.33	1.59	1.77	1.78	1.99	2.42	2.42	ns
LVCMOS33_S4	1.26	1.34	1.41	1.62	3.80	3.93	4.18	4.41	4.37	4.59	5.01	5.06	ns
LVCMOS33_S8	1.26	1.34	1.41	1.62	3.52	3.65	3.90	4.13	4.09	4.31	4.73	4.78	ns
LVCMOS33_S12	1.26	1.34	1.41	1.62	3.09	3.21	3.46	3.69	3.65	3.87	4.29	4.34	ns
LVCMOS33_S16	1.26	1.34	1.41	1.62	3.40	3.52	3.77	4.00	3.97	4.18	4.60	4.65	ns
LVCMOS33_F4	1.26	1.34	1.41	1.62	3.26	3.38	3.64	3.86	3.83	4.04	4.46	4.51	ns
LVCMOS33_F8	1.26	1.34	1.41	1.62	2.74	2.87	3.12	3.35	3.31	3.52	3.95	4.00	ns
LVCMOS33_F12	1.26	1.34	1.41	1.62	2.55	2.68	2.93	3.16	3.12	3.34	3.76	3.81	ns
LVCMOS33_F16	1.26	1.34	1.41	1.62	2.55	2.68	2.93	3.16	3.12	3.34	3.76	3.81	ns
LVCMOS25_S4	1.12	1.20	1.27	1.43	3.13	3.26	3.51	3.72	3.70	3.91	4.34	4.37	ns
LVCMOS25_S8	1.12	1.20	1.27	1.43	2.88	3.01	3.26	3.49	3.45	3.67	4.09	4.14	ns
LVCMOS25_S12	1.12	1.20	1.27	1.43	2.48	2.60	2.85	3.08	3.05	3.26	3.68	3.73	ns
LVCMOS25_S16	1.12	1.20	1.27	1.43	2.82	2.94	3.20	3.43	3.39	3.60	4.03	4.08	ns
LVCMOS25_F4	1.12	1.20	1.27	1.43	2.74	2.87	3.12	3.35	3.31	3.52	3.95	4.00	ns
LVCMOS25_F8	1.12	1.20	1.27	1.43	2.18	2.30	2.56	2.79	2.75	2.96	3.39	3.44	ns
LVCMOS25_F12	1.12	1.20	1.27	1.43	2.16	2.29	2.54	2.77	2.73	2.95	3.37	3.42	ns
LVCMOS25_F16	1.12	1.20	1.27	1.43	2.01	2.13	2.39	2.61	2.58	2.79	3.21	3.26	ns
LVCMOS18_S4	0.74	0.83	0.89	0.94	1.62	1.74	1.99	2.19	2.19	2.40	2.82	2.84	ns
LVCMOS18_S8	0.74	0.83	0.89	0.94	2.18	2.30	2.56	2.79	2.75	2.96	3.39	3.44	ns
LVCMOS18_S12	0.74	0.83	0.89	0.94	2.18	2.30	2.56	2.79	2.75	2.96	3.39	3.44	ns
LVCMOS18_S16	0.74	0.83	0.89	0.94	1.52	1.65	1.90	2.13	2.09	2.31	2.73	2.78	ns
LVCMOS18_S24	0.74	0.83	0.89	0.94	1.60	1.72	1.98	2.21	2.17	2.38	2.81	2.86	ns
LVCMOS18_F4	0.74	0.83	0.89	0.94	1.45	1.57	1.82	2.05	2.01	2.23	2.65	2.70	ns
LVCMOS18_F8	0.74	0.83	0.89	0.94	1.68	1.80	2.06	2.29	2.25	2.46	2.89	2.94	ns
LVCMOS18_F12	0.74	0.83	0.89	0.94	1.68	1.80	2.06	2.29	2.25	2.46	2.89	2.94	ns
LVCMOS18_F16	0.74	0.83	0.89	0.94	1.40	1.52	1.77	2.00	1.97	2.18	2.60	2.65	ns
LVCMOS18_F24	0.74	0.83	0.89	0.94	1.34	1.46	1.71	1.94	1.90	2.12	2.54	2.59	ns
LVCMOS15_S4	0.77	0.86	0.93	0.98	2.05	2.18	2.43	2.50	2.62	2.84	3.26	3.15	ns
LVCMOS15_S8	0.77	0.86	0.93	0.98	2.09	2.21	2.46	2.69	2.65	2.87	3.29	3.34	ns
LVCMOS15_S12	0.77	0.86	0.93	0.98	1.59	1.71	1.96	2.19	2.15	2.37	2.79	2.84	ns
LVCMOS15_S16	0.77	0.86	0.93	0.98	1.59	1.71	1.96	2.19	2.15	2.37	2.79	2.84	ns

Table 16: **3.3V IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
LVCMOS15_F4	0.77	0.86	0.93	0.98	1.85	1.97	2.23	2.27	2.42	2.63	3.06	2.92	ns
LVCMOS15_F8	0.77	0.86	0.93	0.98	1.60	1.72	1.98	2.21	2.17	2.38	2.81	2.86	ns
LVCMOS15_F12	0.77	0.86	0.93	0.98	1.35	1.47	1.73	1.96	1.92	2.13	2.56	2.61	ns
LVCMOS15_F16	0.77	0.86	0.93	0.98	1.34	1.46	1.71	1.94	1.90	2.12	2.54	2.59	ns
LVCMOS12_S4	0.87	0.95	1.02	1.08	2.57	2.69	2.95	3.18	3.14	3.35	3.78	3.83	ns
LVCMOS12_S8	0.87	0.95	1.02	1.08	2.09	2.21	2.46	2.69	2.65	2.87	3.29	3.34	ns
LVCMOS12_S12	0.87	0.95	1.02	1.08	1.79	1.91	2.17	2.40	2.36	2.57	2.99	3.05	ns
LVCMOS12_F4	0.87	0.95	1.02	1.08	1.98	2.10	2.35	2.58	2.54	2.76	3.18	3.23	ns
LVCMOS12_F8	0.87	0.95	1.02	1.08	1.54	1.66	1.92	2.15	2.11	2.32	2.75	2.80	ns
LVCMOS12_F12	0.87	0.95	1.02	1.08	1.38	1.51	1.76	1.97	1.95	2.16	2.59	2.62	ns
SSTL135_S	0.67	0.75	0.82	0.87	1.35	1.47	1.73	1.93	1.92	2.13	2.56	2.58	ns
SSTL15_S	0.60	0.68	0.75	0.80	1.30	1.43	1.68	1.88	1.87	2.09	2.51	2.53	ns
SSTL18_I_S	0.67	0.75	0.82	0.87	1.67	1.79	2.04	2.24	2.23	2.45	2.87	2.89	ns
SSTL18_II_S	0.67	0.75	0.82	0.87	1.31	1.43	1.68	1.91	1.87	2.09	2.51	2.56	ns
DIFF_SSTL135_S	0.68	0.76	0.83	0.87	1.35	1.47	1.73	1.93	1.92	2.13	2.56	2.58	ns
DIFF_SSTL15_S	0.68	0.76	0.83	0.87	1.30	1.43	1.68	1.88	1.87	2.09	2.51	2.53	ns
DIFF_SSTL18_I_S	0.71	0.79	0.86	0.87	1.68	1.80	2.06	2.24	2.25	2.46	2.89	2.89	ns
DIFF_SSTL18_II_S	0.71	0.79	0.86	0.87	1.38	1.51	1.76	1.94	1.95	2.17	2.59	2.59	ns
SSTL135_F	0.67	0.75	0.82	0.87	1.12	1.24	1.49	1.71	1.69	1.90	2.32	2.36	ns
SSTL15_F	0.60	0.68	0.75	0.80	1.07	1.19	1.45	1.68	1.64	1.85	2.28	2.33	ns
SSTL18_I_F	0.67	0.75	0.82	0.87	1.12	1.24	1.49	1.72	1.69	1.90	2.32	2.37	ns
SSTL18_II_F	0.67	0.75	0.82	0.87	1.12	1.24	1.49	1.71	1.69	1.90	2.32	2.36	ns
DIFF_SSTL135_F	0.68	0.76	0.83	0.87	1.12	1.24	1.49	1.71	1.69	1.90	2.32	2.36	ns
DIFF_SSTL15_F	0.68	0.76	0.83	0.87	1.07	1.19	1.45	1.68	1.64	1.85	2.28	2.33	ns
DIFF_SSTL18_I_F	0.71	0.79	0.86	0.87	1.23	1.35	1.60	1.80	1.79	2.01	2.43	2.45	ns
DIFF_SSTL18_II_F	0.71	0.79	0.86	0.87	1.21	1.33	1.59	1.79	1.78	1.99	2.42	2.44	ns

Table 17 specifies the values of T_{IOTPHZ} and $T_{IOIBUFDISABLE}$. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). $T_{IOIBUFDISABLE}$ is described as the IOB delay from IBUFDISABLE to O output. In HR I/O banks, the internal IN_TERM termination turn-off time is always faster than T_{IOTPHZ} when the INTERMDISABLE pin is used.

Table 17: **IOB 3-state Output Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{IOTPHZ}	T input to pad high-impedance	2.06	2.19	2.37	2.19	ns
$T_{IOIBUFDISABLE}$	IBUF turn-on time from IBUFDISABLE to O output	2.11	2.30	2.60	2.30	ns

Input Serializer/Deserializer Switching Characteristics

Table 20: **ISERDES Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Setup/Hold for Control Lines						
$T_{ISCCK\_BITSLIP}$/ $T_{ISCKC\_BITSLIP}$	BITSLIP pin setup/hold with respect to CLKDIV	0.01/0.14	0.02/0.15	0.02/0.17	0.02/0.21	ns
T_{ISCCK_CE} / T_{ISCKC_CE}[(2)]	CE pin setup/hold with respect to CLK (for CE1)	0.45/–0.01	0.50/–0.01	0.72/–0.01	0.35/–0.11	ns
T_{ISCCK_CE2} / T_{ISCKC_CE2}[(2)]	CE pin setup/hold with respect to CLKDIV (for CE2)	–0.10/0.33	–0.10/0.36	–0.10/0.40	–0.17/0.40	ns
Setup/Hold for Data Lines						
T_{ISDCK_D} /T_{ISCKD_D}	D pin setup/hold with respect to CLK	–0.02/0.12	–0.02/0.14	–0.02/0.17	–0.04/0.19	ns
T_{ISDCK_DDLY} /T_{ISCKD_DDLY}	DDLY pin setup/hold with respect to CLK (using IDELAY)[(1)]	–0.02/0.12	–0.02/0.14	–0.02/0.17	–0.03/0.19	ns
$T_{ISDCK\_D\_DDR}$ /$T_{ISCKD\_D\_DDR}$	D pin setup/hold with respect to CLK at DDR mode	–0.02/0.12	–0.02/0.14	–0.02/0.17	–0.04/0.19	ns
$T_{ISDCK\_DDLY\_DDR}$/ $T_{ISCKD\_DDLY\_DDR}$	D pin setup/hold with respect to CLK at DDR mode (using IDELAY)[(1)]	0.12/0.12	0.14/0.14	0.17/0.17	0.19/0.19	ns
Sequential Delays						
T_{ISCKO_Q}	CLKDIV to out at Q pin	0.53	0.54	0.66	0.67	ns
Propagation Delays						
T_{ISDO_DO}	D input to DO output pin	0.11	0.11	0.13	0.14	ns

Notes:
1. Recorded at 0 tap value.
2. T_{ISCCK_CE2} and T_{ISCKC_CE2} are reported as T_{ISCCK_CE}/T_{ISCKC_CE} in TRACE report.

Table 23: **IO_FIFO Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
IO_FIFO Clock to Out Delays						
T_{OFFCKO_DO}	RDCLK to Q outputs	0.55	0.60	0.68	0.81	ns
T_{CKO_FLAGS}	Clock to IO_FIFO flags	0.55	0.61	0.77	0.55	ns
Setup/Hold						
T_{CCK_D}/T_{CKC_D}	D inputs to WRCLK	0.47/0.02	0.51/0.02	0.58/0.02	0.76/–0.05	ns
$T_{IFFCCK\_WREN}/T_{IFFCKC\_WREN}$	WREN to WRCLK	0.42/–0.01	0.47/–0.01	0.53/–0.01	0.70/–0.05	ns
$T_{OFFCCK\_RDEN}/T_{OFFCKC\_RDEN}$	RDEN to RDCLK	0.53/0.02	0.58/0.02	0.66/0.02	0.79/–0.02	ns
Minimum Pulse Width						
$T_{PWH\_IO\_FIFO}$	RESET, RDCLK, WRCLK	1.62	2.15	2.15	2.15	ns
$T_{PWL\_IO\_FIFO}$	RESET, RDCLK, WRCLK	1.62	2.15	2.15	2.15	ns
Maximum Frequency						
F_{MAX}	RDCLK and WRCLK	266.67	200.00	200.00	200.00	MHz

CLB Distributed RAM Switching Characteristics (SLICEM Only)

Table 25: **CLB Distributed RAM Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Sequential Delays						
T_{SHCKO}	Clock to A – B outputs	0.98	1.09	1.32	1.54	ns, Max
T_{SHCKO_1}	Clock to AMUX – BMUX outputs	1.37	1.53	1.86	2.18	ns, Max
Setup and Hold Times Before/After Clock CLK						
T_{DS_LRAM}/T_{DH_LRAM}	A – D inputs to CLK	0.54/0.28	0.60/0.30	0.72/0.35	0.96/0.40	ns, Min
T_{AS_LRAM}/T_{AH_LRAM}	Address An inputs to clock	0.27/0.55	0.30/0.60	0.37/0.70	0.43/0.71	ns, Min
	Address An inputs through MUXs and/or carry logic to clock	0.69/0.18	0.77/0.21	0.94/0.26	1.11/0.29	ns, Min
T_{WS_LRAM}/T_{WH_LRAM}	WE input to clock	0.38/0.10	0.43/0.12	0.53/0.17	0.62/0.13	ns, Min
$T_{CECK\_LRAM}/T_{CKCE\_LRAM}$	CE input to CLK	0.39/0.10	0.44/0.11	0.53/0.17	0.63/0.12	ns, Min
Clock CLK						
T_{MPW_LRAM}	Minimum pulse width	1.05	1.13	1.25	0.82	ns, Min
T_{MCP}	Minimum clock period	2.10	2.26	2.50	1.64	ns, Min

Notes:

1. A Zero “0” Hold Time listing indicates no hold time or a negative hold time.
2. T_{SHCKO} also represents the CLK to XMUX output. Refer to TRACE report for the CLK to XMUX path.

CLB Shift Register Switching Characteristics (SLICEM Only)

Table 26: **CLB Shift Register Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Sequential Delays						
T_{REG}	Clock to A – D outputs	1.19	1.33	1.61	1.89	ns, Max
T_{REG_MUX}	Clock to AMUX – DMUX output	1.58	1.77	2.15	2.53	ns, Max
T_{REG_M31}	Clock to DMUX output via M31 output	1.12	1.23	1.46	1.68	ns, Max
Setup and Hold Times Before/After Clock CLK						
$T_{WS\_SHFREG}/T_{WH\_SHFREG}$	WE input	0.37/0.10	0.41/0.12	0.51/0.17	0.59/0.13	ns, Min
$T_{CECK\_SHFREG}/T_{CKCE\_SHFREG}$	CE input to CLK	0.37/0.10	0.42/0.11	0.52/0.17	0.60/0.12	ns, Min
$T_{DS\_SHFREG}/T_{DH\_SHFREG}$	A – D inputs to CLK	0.33/0.34	0.37/0.37	0.44/0.43	0.54/0.47	ns, Min
Clock CLK						
T_{MPW_SHFREG}	Minimum pulse width	0.77	0.86	0.98	1.04	ns, Min

Notes:

1. A Zero “0” Hold Time listing indicates no hold time or a negative hold time.

Block RAM and FIFO Switching Characteristics

Table 27: **Block RAM and FIFO Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Block RAM and FIFO Clock-to-Out Delays						
T_{RCKO_DO} and $T_{RCKO\_DO\_REG}$[1]	Clock CLK to DOUT output (without output register)[2][3]	1.85	2.13	2.46	2.87	ns, Max
	Clock CLK to DOUT output (with output register)[4][5]	0.64	0.74	0.89	1.02	ns, Max
$T_{RCKO\_DO\_ECC}$ and $T_{RCKO\_DO\_ECC\_REG}$	Clock CLK to DOUT output with ECC (without output register)[2][3]	2.77	3.04	3.84	5.30	ns, Max
	Clock CLK to DOUT output with ECC (with output register)[4][5]	0.73	0.81	0.94	1.11	ns, Max
$T_{RCKO\_DO\_CASCOUT}$ and $T_{RCKO\_DO\_CASCOUT\_REG}$	Clock CLK to DOUT output with cascade (without output register)[2]	2.61	2.88	3.30	3.76	ns, Max
	Clock CLK to DOUT output with cascade (with output register)[4]	1.16	1.28	1.46	1.56	ns, Max
T_{RCKO_FLAGS}	Clock CLK to FIFO flags outputs[6]	0.76	0.87	1.05	1.14	ns, Max
$T_{RCKO\_POINTERS}$	Clock CLK to FIFO pointers outputs[7]	0.94	1.02	1.15	1.30	ns, Max
$T_{RCKO\_PARITY\_ECC}$	Clock CLK to ECCPARITY in ECC encode only mode	0.78	0.85	0.94	1.10	ns, Max
$T_{RCKO\_SDBIT\_ECC}$ and $T_{RCKO\_SDBIT\_ECC\_REG}$	Clock CLK to BITERR (without output register)	2.56	2.81	3.55	4.90	ns, Max
	Clock CLK to BITERR (with output register)	0.68	0.76	0.89	1.05	ns, Max
$T_{RCKO\_RDADDR\_ECC}$ and $T_{RCKO\_RDADDR\_ECC\_REG}$	Clock CLK to RDADDR output with ECC (without output register)	0.75	0.88	1.07	1.15	ns, Max
	Clock CLK to RDADDR output with ECC (with output register)	0.84	0.93	1.08	1.29	ns, Max
Setup and Hold Times Before/After Clock CLK						
$T_{RCCK\_ADDRA}/T_{RCKC\_ADDRA}$	ADDR inputs[8]	0.45/0.31	0.49/0.33	0.57/0.36	0.77/0.45	ns, Min
$T_{RDCK\_DI\_WF\_NC}/T_{RCKD\_DI\_WF\_NC}$	Data input setup/hold time when block RAM is configured in WRITE_FIRST or NO_CHANGE mode[9]	0.58/0.60	0.65/0.63	0.74/0.67	0.92/0.76	ns, Min
$T_{RDCK\_DI\_RF}/T_{RCKD\_DI\_RF}$	Data input setup/hold time when block RAM is configured in READ_FIRST mode[9]	0.20/0.29	0.22/0.34	0.25/0.41	0.29/0.38	ns, Min
$T_{RDCK\_DI\_ECC}/T_{RCKD\_DI\_ECC}$	DIN inputs with block RAM ECC in standard mode[9]	0.50/0.43	0.55/0.46	0.63/0.50	0.78/0.54	ns, Min
$T_{RDCK\_DI\_ECCW}/T_{RCKD\_DI\_ECCW}$	DIN inputs with block RAM ECC encode only[9]	0.93/0.43	1.02/0.46	1.17/0.50	1.38/0.48	ns, Min
$T_{RDCK\_DI\_ECC\_FIFO}/T_{RCKD\_DI\_ECC\_FIFO}$	DIN inputs with FIFO ECC in standard mode[9]	1.04/0.56	1.15/0.59	1.32/0.64	1.55/0.77	ns, Min
$T_{RCCK\_INJECTBITERR}/T_{RCKC\_INJECTBITERR}$	Inject single/double bit error in ECC mode	0.58/0.35	0.64/0.37	0.74/0.40	0.92/0.48	ns, Min
T_{RCCK_EN}/T_{RCKC_EN}	Block RAM enable (EN) input	0.35/0.20	0.39/0.21	0.45/0.23	0.57/0.26	ns, Min
$T_{RCCK\_REGCE}/T_{RCKC\_REGCE}$	CE input of output register	0.24/0.15	0.29/0.15	0.36/0.16	0.40/0.19	ns, Min
$T_{RCCK\_RSTREG}/T_{RCKC\_RSTREG}$	Synchronous RSTREG input	0.29/0.07	0.32/0.07	0.35/0.07	0.41/0.07	ns, Min

Table 44: **Data Input Setup and Hold Times Relative to a Forwarded Clock Input Pin Using BUFIO**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Input Setup and Hold Time Relative to a Forwarded Clock Input Pin Using BUFIO for SSTL15 Standard.						
T_{PSCS}/T_{PHCS}	Setup and hold of I/O clock	–0.38/1.31	–0.38/1.46	–0.38/1.76	–0.16/1.89	ns

Table 45: **Sample Window**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{SAMP}	Sampling error at receiver pins[1]	0.59	0.64	0.70	0.70	ns
T_{SAMP_BUFIO}	Sampling error at receiver pins using BUFIO[2]	0.35	0.40	0.46	0.46	ns

Notes:

1. This parameter indicates the total sampling error of the Artix-7 FPGAs DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the MMCM to capture the DDR input registers' edges of operation. These measurements include:
   - CLK0 MMCM jitter
   - MMCM accuracy (phase offset)
   - MMCM phase shift resolution

   These measurements do not include package or clock tree skew.
2. This parameter indicates the total sampling error of the Artix-7 FPGAs DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the BUFIO clock network and IDELAY to capture the DDR input registers' edges of operation. These measurements do not include package or clock tree skew.

Additional Package Parameter Guidelines

The parameters in this section provide the necessary values for calculating timing budgets for Artix-7 FPGA clock transmitter and receiver data-valid windows.

Table 46: **Package Skew**

Symbol	Description	Device	Package	Value	Units
$T_{PKGSKEW}$	Package skew[1]	XC7A100T	CSG324	113	ps
			FTG256	120	ps
			FGG484	144	ps
			FGG676	153	ps
		XC7A200T	SBG484	111	ps
			FBG484	109	ps
			FBG676	121	ps
			FFG1156	151	ps

Notes:

1. These values represent the worst-case skew between any two SelectIO resources in the package: shortest delay to longest delay from die pad to ball.
2. Package delay information is available for these device/package combinations. This information can be used to deskew the package.

GTP Transceiver Specifications

GTP Transceiver DC Input and Output Levels

Table 47 summarizes the DC output specifications of the GTP transceivers in Artix-7 FPGAs. Consult UG482: *7 Series FPGAs GTP Transceiver User Guide* for further details.

Table 47: **GTP Transceiver DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV_{PPOUT}	Differential peak-to-peak output voltage(1)	Transmitter output swing is set to maximum setting	–	–	1000	mV
$V_{CMOUTDC}$	DC common mode output voltage	Equation based	$V_{MGTAVTT} – DV_{PPOUT}/4$			mV
R_{OUT}	Differential output resistance		–	100	–	Ω
$V_{CMOUTAC}$	Common mode output voltage: AC coupled		1/2 $V_{MGTAVTT}$			mV
T_{OSKEW}	Transmitter output pair (TXP and TXN) intra-pair skew (FFG, FBG, SBG packages)		–	–	10	ps
	Transmitter output pair (TXP and TXN) intra-pair skew (FGG, FTG, CSG packages)		–	–	12	ps
DV_{PPIN}	Differential peak-to-peak input voltage	External AC coupled	150	–	2000	mV
V_{IN}	Absolute input voltage	DC coupled $V_{MGTAVTT}$ = 1.2V	–200	–	$V_{MGTAVTT}$	mV
V_{CMIN}	Common mode input voltage	DC coupled $V_{MGTAVTT}$ = 1.2V	–	2/3 $V_{MGTAVTT}$	–	mV
R_{IN}	Differential input resistance		–	100	–	Ω
C_{EXT}	Recommended external AC coupling capacitor(2)		–	100	–	nF

Notes:

1. The output swing and preemphasis levels are programmable using the attributes discussed in UG482: *7 Series FPGAs GTP Transceiver User Guide* and can result in values lower than reported in this table.
2. Other values can be used as appropriate to conform to specific protocols and standards.

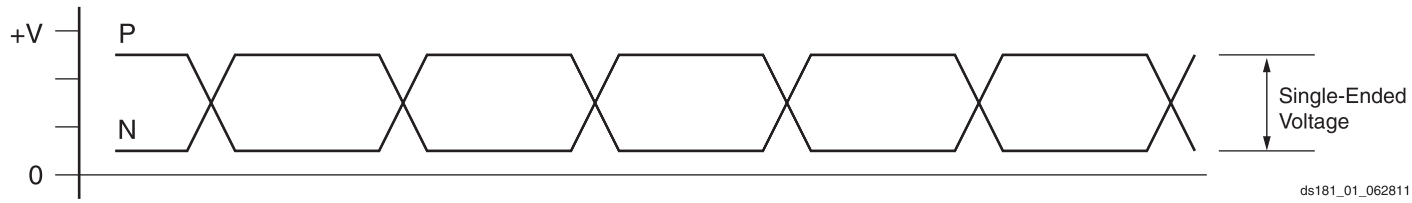

Figure 1: **Single-Ended Peak-to-Peak Voltage**

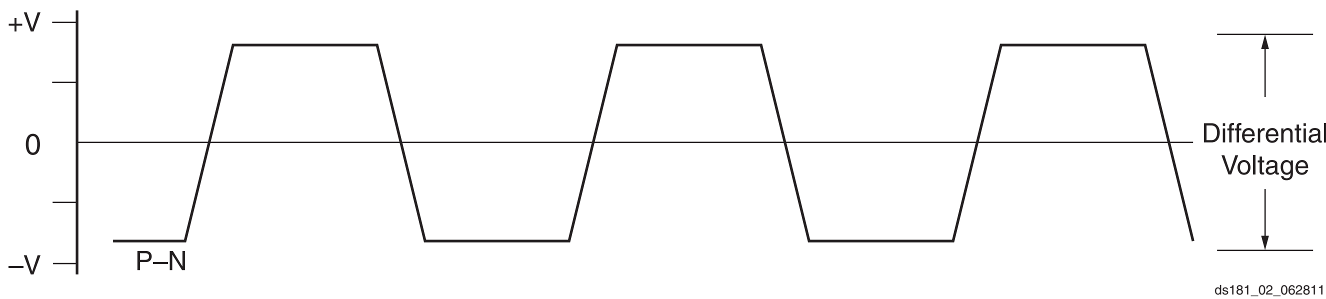

Figure 2: **Differential Peak-to-Peak Voltage**

Table 55: **GTP Transceiver Receiver Switching Characteristics**

Symbol	Description		Min	Typ	Max	Units
F_{GTPRX}	Serial data rate	RX oversampler not enabled	0.500	–	F_{GTPMAX}	Gb/s
$T_{RXELECIDLE}$	Time for RXELECIDLE to respond to loss or restoration of data		–	10	–	ns
$RX_{OOBVDPP}$	OOB detect threshold peak-to-peak		60	–	150	mV
RX_{SST}	Receiver spread-spectrum tracking(1)	Modulated @ 33 KHz	–5000	–	5000	ppm
RX_{RL}	Run length (CID)		–	–	512	UI
RX_{PPMTOL}	Data/REFCLK PPM offset tolerance		–1250	–	1250	ppm
SJ Jitter Tolerance(2)						
$JT\_SJ_{6.6}$	Sinusoidal Jitter(3)	6.6 Gb/s	0.44	–	–	UI
$JT\_SJ_{5.0}$	Sinusoidal Jitter(3)	5.0 Gb/s	0.44	–	–	UI
$JT\_SJ_{4.25}$	Sinusoidal Jitter(3)	4.25 Gb/s	0.44	–	–	UI
$JT\_SJ_{3.75}$	Sinusoidal Jitter(3)	3.75 Gb/s	0.44	–	–	UI
$JT\_SJ_{3.2}$	Sinusoidal Jitter(3)	3.2 Gb/s(4)	0.45	–	–	UI
$JT\_SJ_{3.2L}$	Sinusoidal Jitter(3)	3.2 Gb/s(5)	0.45	–	–	UI
$JT\_SJ_{2.5}$	Sinusoidal Jitter(3)	2.5 Gb/s(6)	0.5	–	–	UI
$JT\_SJ_{1.25}$	Sinusoidal Jitter(3)	1.25 Gb/s(7)	0.5	–	–	UI
JT_SJ_{500}	Sinusoidal Jitter(3)	500 Mb/s	0.4	–	–	UI
SJ Jitter Tolerance with Stressed Eye(2)						
$JT\_TJSE_{3.2}$	Total Jitter with Stressed Eye(8)	3.2 Gb/s	0.70	–	–	UI
$JT\_TJSE_{6.6}$		6.6 Gb/s	0.70	–	–	UI
$JT\_SJSE_{3.2}$	Sinusoidal Jitter with Stressed Eye(8)	3.2 Gb/s	0.1	–	–	UI
$JT\_SJSE_{6.6}$		6.6 Gb/s	0.1	–	–	UI

Notes:

1. Using RXOUT_DIV = 1, 2, and 4.
2. All jitter values are based on a bit error ratio of $1e^{-12}$.
3. The frequency of the injected sinusoidal jitter is 10 MHz.
4. PLL frequency at 3.2 GHz and RXOUT_DIV = 2.
5. PLL frequency at 1.6 GHz and RXOUT_DIV = 1.
6. PLL frequency at 2.5 GHz and RXOUT_DIV = 2.
7. PLL frequency at 2.5 GHz and RXOUT_DIV = 4.
8. Composite jitter.

GTP Transceiver Protocol Jitter Characteristics

For Table 56 through Table 60, the UG482: *7 Series FPGAs GTP Transceiver User Guide* contains recommended settings for optimal usage of protocol specific characteristics.

Table 56: **Gigabit Ethernet Protocol Characteristics**

Description	Line Rate (Mb/s)	Min	Max	Units
Gigabit Ethernet Transmitter Jitter Generation				
Total transmitter jitter (T_TJ)	1250	–	0.24	UI
Gigabit Ethernet Receiver High Frequency Jitter Tolerance				
Total receiver jitter tolerance	1250	0.749	–	UI

Table 57: **XAUI Protocol Characteristics**

Description	Line Rate (Mb/s)	Min	Max	Units
XAUI Transmitter Jitter Generation				
Total transmitter jitter (T_TJ)	3125	–	0.35	UI
XAUI Receiver High Frequency Jitter Tolerance				
Total receiver jitter tolerance	3125	0.65	–	UI

Table 58: **PCI Express Protocol Characteristics[(1)]**

Standard	Description	Line Rate (Mb/s)	Min	Max	Units
PCI Express Transmitter Jitter Generation					
PCI Express Gen 1	Total transmitter jitter	2500	–	0.25	UI
PCI Express Gen 2	Total transmitter jitter	5000	–	0.25	UI
PCI Express Receiver High Frequency Jitter Tolerance					
PCI Express Gen 1	Total receiver jitter tolerance	2500	0.65	–	UI
PCI Express Gen 2[(2)]	Receiver inherent timing error	5000	0.40	–	UI
	Receiver inherent deterministic timing error		0.30	–	UI

Notes:

1. Tested per card electromechanical (CEM) methodology.
2. Using common REFCLK.

Table 59: **CEI-6G Protocol Characteristics**

Description	Line Rate (Mb/s)	Interface	Min	Max	Units
CEI-6G Transmitter Jitter Generation					
Total transmitter jitter[(1)]	4976–6375	CEI-6G-SR	–	0.3	UI
CEI-6G Receiver High Frequency Jitter Tolerance					
Total receiver jitter tolerance[(1)]	4976–6375	CEI-6G-SR	0.6	–	UI

Notes:

1. Tested at most commonly used line rate of 6250 Mb/s using 390.625 MHz reference clock.

Table 60: **CPRI Protocol Characteristics**

Description	Line Rate (Mb/s)	Min	Max	Units
CPRI Transmitter Jitter Generation				
Total transmitter jitter	614.4	–	0.35	UI
	1228.8	–	0.35	UI
	2457.6	–	0.35	UI
	3072.0	–	0.35	UI
	4915.2	–	0.3	UI
	6144.0	–	0.3	UI
CPRI Receiver Frequency Jitter Tolerance				
Total receiver jitter tolerance	614.4	0.65	–	UI
	1228.8	0.65	–	UI
	2457.6	0.65	–	UI
	3072.0	0.65	–	UI
	4915.2[1]	0.60	–	UI
	6144.0[1]	0.60	–	UI

Notes:

1. Tested to CEI-6G-SR.

Integrated Interface Block for PCI Express Designs Switching Characteristics

More information and documentation on solutions for PCI Express designs can be found at:
http://www.xilinx.com/technology/protocols/pciexpress.htm

Table 61: **Maximum Performance for PCI Express Designs**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
$F_{PIPECLK}$	Pipe clock maximum frequency	250.00	250.00	250.00	250.00	MHz
$F_{USERCLK}$	User clock maximum frequency	250.00	250.00	250.00	250.00	MHz
$F_{USERCLK2}$	User clock 2 maximum frequency	250.00	250.00	250.00	250.00	MHz
F_{DRPCLK}	DRP clock maximum frequency	250.00	250.00	250.00	250.00	MHz

XADC Specifications

Table 62: **XADC Specifications**

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
V_{CCADC} = 1.8V ± 5%, V_{REFP} = 1.25V, V_{REFN} = 0V, ADCCLK = 26 MHz, T_j = –40°C to 100°C, Typical values at T_j=+40°C						
ADC Accuracy(1)						
Resolution			12	–	–	Bits
Integral Nonlinearity(2)	INL		–	–	±2	LSBs
Differential Nonlinearity	DNL	No missing codes, guaranteed monotonic	–	–	±1	LSBs
Offset Error		Unipolar operation	–	–	±8	LSBs
		Bipolar operation	–	–	±4	LSBs
Gain Error			–	–	±0.5	%
Offset Matching			–	–	4	LSBs
Gain Matching			–	–	0.3	%
Sample Rate			0.1	–	1	MS/s
Signal to Noise Ratio(2)	SNR	F_{SAMPLE} = 500KS/s, F_{IN} = 20KHz	60	–	–	dB
RMS Code Noise		External 1.25V reference	–	–	2	LSBs
		On-chip reference	–	3	–	LSBs
Total Harmonic Distortion(2)	THD	F_{SAMPLE} = 500KS/s, F_{IN} = 20KHz	70	–	–	dB
ADC Accuracy at Extended Temperatures (-55°C to 125°C)						
Resolution			10	–	–	Bits
Integral Nonlinearity(2)	INL		–	–	±1	LSB (at 10 bits)
Differential Nonlinearity	DNL	No missing codes, guaranteed monotonic	–	–	±1	
Analog Inputs(3)						
ADC Input Ranges		Unipolar operation	0	–	1	V
		Bipolar operation	–0.5	–	+0.5	V
		Unipolar common mode range (FS input)	0	–	+0.5	V
		Bipolar common mode range (FS input)	+0.5	–	+0.6	V
Maximum External Channel Input Ranges		Adjacent analog channels set within these ranges should not corrupt measurements on adjacent channels	–0.1	–	V_{CCADC}	V
Auxiliary Channel Full Resolution Bandwidth	FRBW		250	–	–	KHz
On-Chip Sensors						
Temperature Sensor Error		T_j = –40°C to 100°C	–	–	±4	°C
		T_j = –55°C to +125°C	–	–	±6	°C
Supply Sensor Error		Measurement range of V_{CCAUX} 1.8V ±5% T_j = –40°C to +100°C	–	–	±1	%
		Measurement range of V_{CCAUX} 1.8V ±5% T_j = –55°C to +125°C	–	–	±2	%
Conversion Rate(4)						
Conversion Time - Continuous	t_{CONV}	Number of ADCCLK cycles	26	–	32	Cycles
Conversion Time - Event	t_{CONV}	Number of CLK cycles	–	–	21	Cycles
DRP Clock Frequency	DCLK	DRP clock frequency	8	–	250	MHz
ADC Clock Frequency	ADCCLK	Derived from DCLK	1	–	26	MHz

Table 63: **Configuration Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Internal Configuration Access Port						
F_{ICAPCK}	Internal configuration access port (ICAPE2) clock frequency	100.00	100.00	100.00	70.00	MHz, Max
Master/Slave Serial Mode Programming Switching						
T_{DCCK}/T_{CCKD}	DIN setup/hold	4.00/0.00	4.00/0.00	4.00/0.00	5.00/0.00	ns, Min
T_{CCO}	DOUT clock to out	8.00	8.00	8.00	9.00	ns, Max
SelectMAP Mode Programming Switching						
T_{SMDCCK}/T_{SMCCKD}	D[31:00] setup/hold	4.00/0.00	4.00/0.00	4.00/0.00	4.50/0.00	ns, Min
$T_{SMCSCCK}/T_{SMCCKCS}$	CSI_B setup/hold	4.00/0.00	4.00/0.00	4.00/0.00	5.00/0.00	ns, Min
T_{SMWCCK}/T_{SMCCKW}	RDWR_B setup/hold	10.00/0.00	10.00/0.00	10.00/0.00	12.00/0.00	ns, Min
$T_{SMCKCSO}$	CSO_B clock to out (330 Ω pull-up resistor required)	7.00	7.00	7.00	8.00	ns, Max
T_{SMCO}	D[31:00] clock to out in readback	8.00	8.00	8.00	10.00	ns, Max
F_{RBCCK}	Readback frequency	100.00	100.00	100.00	70.00	MHz, Max
Boundary-Scan Port Timing Specifications						
T_{TAPTCK}/T_{TCKTAP}	TMS and TDI setup/hold	3.00/2.00	3.00/2.00	3.00/2.00	3.00/2.00	ns, Min
T_{TCKTDO}	TCK falling edge to TDO output	7.00	7.00	7.00	8.50	ns, Max
F_{TCK}	TCK frequency	66.00	66.00	66.00	50.00	MHz, Max
BPI Flash Master Mode Programming Switching						
T_{BPICCO}(2)	A[28:00], RS[1:0], FCS_B, FOE_B, FWE_B, ADV_B clock to out	8.50	8.50	8.50	10.00	ns, Max
T_{BPIDCC}/T_{BPICCD}	D[15:00] setup/hold	4.00/0.00	4.00/0.00	4.00/0.00	4.50/0.00	ns, Min
SPI Flash Master Mode Programming Switching						
T_{SPIDCC}/T_{SPICCD}	D[03:00] setup/hold	3.00/0.00	3.00/0.00	3.00/0.00	3.00/0.00	ns, Min
T_{SPICCM}	MOSI clock to out	8.00	8.00	8.00	9.00	ns, Max
$T_{SPICCFC}$	FCS_B clock to out	8.00	8.00	8.00	9.00	ns, Max

Notes:

1. To support longer delays in configuration, use the design solutions described in UG470: *7 Series FPGA Configuration User Guide*.
2. Only during configuration, the last edge is determined by a weak pull-up/pull-down resistor in the I/O.

eFUSE Programming Conditions

Table 64 lists the programming conditions specifically for eFUSE. For more information, see UG470: *7 Series FPGA Configuration User Guide*.

Table 64: **eFUSE Programming Conditions**(1)

Symbol	Description	Min	Typ	Max	Units
I_{FS}	V_{CCAUX} supply current	–	–	115	mA
t_j	Temperature range	15	–	125	°C

Notes:

1. The FPGA must not be configured during eFUSE programming.

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